



**TO-92MOD Plastic-Encapsulate Transistors**

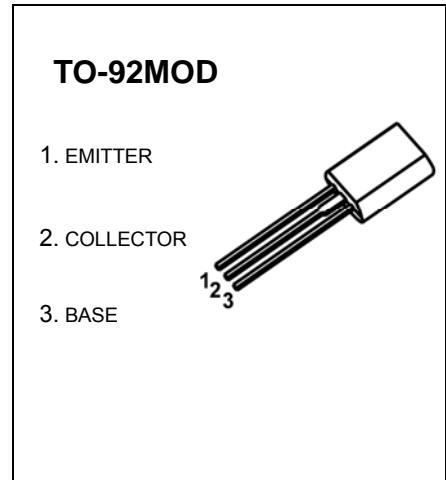
**2SD667,2SD667A** TRANSISTOR (NPN)

**FEATURES**

- Low Frequency Power Amplifier
- Complementary Pair with 2SB647/A

**MAXIMUM RATINGS (Ta=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector- Base Voltage	120	V
V <sub>CEO</sub>	Collector-Emitter Voltage 2SD667	80	V
	2SD667A	100	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current -Continuous	1	A
P <sub>C</sub>	Collector Power Dissipation	900	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C



**ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =10μA, I <sub>E</sub> =0	120			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	2SD667	80		V
			2SD667A	100		V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10μA, I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =100V, I <sub>E</sub> =0			10	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =4V, I <sub>C</sub> =0			10	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =150mA	2SD667	60		320
			2SD667A	60		320
	h <sub>FE(2)</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =500mA	30			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA			1	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =150mA			1.5	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =150mA		140		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		12		pF

**CLASSIFICATION OF h<sub>FE(1)</sub>**

Rank		B	C	D
Range	2SD667	60-120	100-200	160-320
	2SD667A	60-120	100-200	160-320